Data Sheet

Central™
Semiconductor Corp.
145 Adams Avenue, Hauppauge, NY 11788 USA
Tel: (631) 435-1110 • Fax: (631) 435-1824

Manufacturers of World Class Discrete Semiconductors

CBR4M-L010M SERIES

GLASS PASSIVATED JUNCTION SILICON BRIDGE RECTIFIER 4.0 AMP, 100 THRU 1000 VOLTS

CASE DMM

DESCRIPTION

The CENTRAL SEMICONDUCTOR CBR4M-L010M series types are silicon single phase full wave bridge rectifiers designed for general purpose, high current applications. **THIS DEVICE IS MANUFACTURED WITH A GLASS PASSIVATED CHIP FOR OPTIMUM RELIABILITY.**

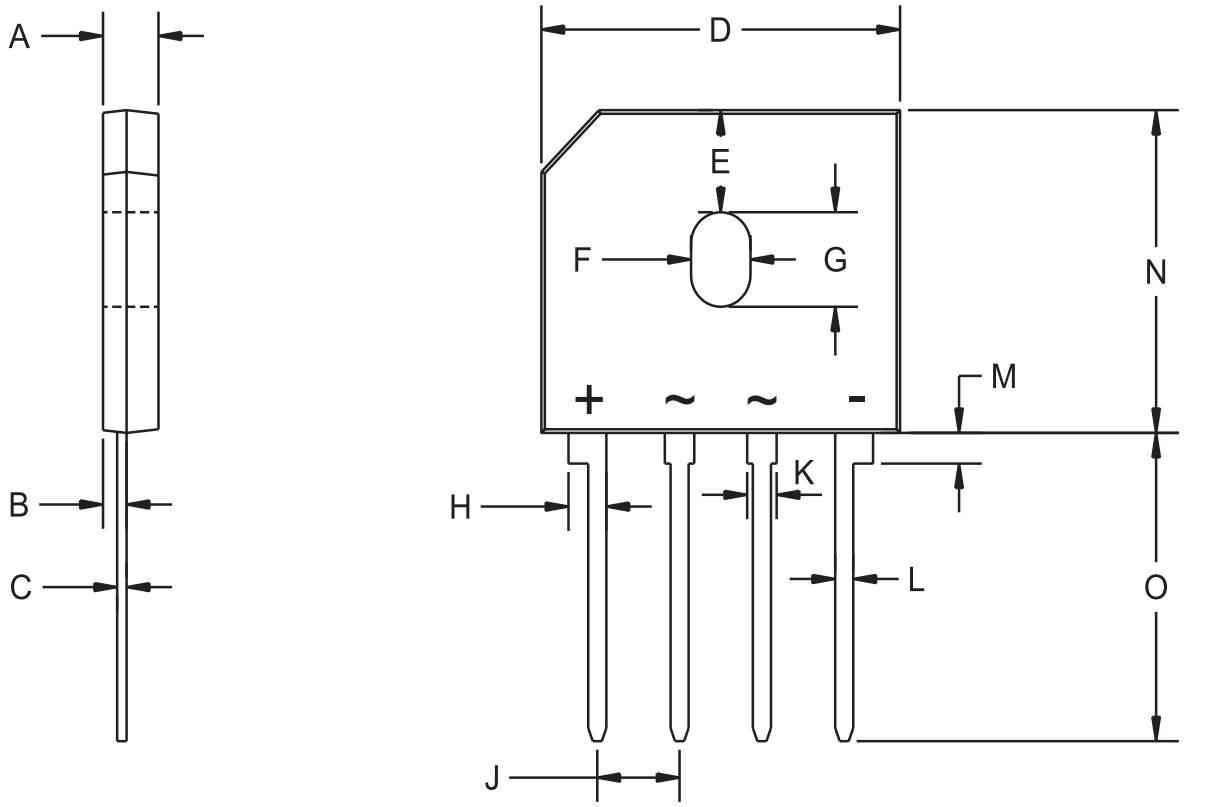
MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

	SYMBOL	CBR4M -L010M	CBR4M -L020M	CBR4M -L040M	CBR4M -L060M	CBR4M -L080M	CBR4M -L100M	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	100	200	400	600	800	1000	V
DC Blocking Voltage	V_R	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	140	280	420	560	700	V
Average Forward Current (T_C=100°C)	I_O			4.0				A
Peak Forward Surge Current	I_{FSM}			150				A
Operating and Storage Junction Temperature	T_J,T_{stg}			-65 to +150				°C
Thermal Resistance	Θ_{JC}			4.0				°C/W

ELECTRICAL CHARACTERISTICS PER DIODE (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	V_R=Rated V_{RRM}			5.0	μA
I_R	V_R=Rated V_{RRM}, T_C=100°C			500	μA
V_F	I_F=4.0A			1.0	V
C_J	V_R=4.0V, f=1.0MHz		270		pF

CASE DMM - MECHANICAL OUTLINE



R1

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.130	0.140	3.30	3.56
B	0.030	0.040	0.76	1.02
C	0.018	0.022	0.46	0.56
D	0.860	0.880	21.84	22.35
E	0.230		5.85	
F	0.150		3.81	
G	0.215		5.46	
H	0.085	0.100	2.16	2.54
J	0.190	0.210	4.83	5.33
K	0.065	0.080	1.65	2.03
L	0.040	0.050	1.02	1.27
M	0.060	0.080	1.52	2.03
N	0.720	0.740	18.30	18.80
O	0.690	0.710	17.53	18.03

Case DMM (REV: R1)

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R1 (18- April 2002)